FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

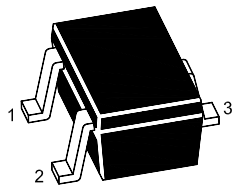
FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.
TEL: 852-2790 0314 FAX: 852-2790 0206

MMFTN3018W

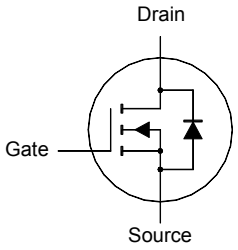
Silicon N-Channel MOSFET

Applications

• Interfacing, switching



1. Gate 2. Source 3. Drain
SOT-323 Plastic Package



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	30	V
Gate Source Voltage	V_{GSS}	± 20	V
Drain Current	I_D	100	mA
Drain Current (Pulsed)	I_{DP} [1)]	400	mA
Total Power Dissipation	P_{tot} [2)]	200	mW
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_s	- 55 to + 150	°C

Thermal Resistance

Parameter	Symbol	Value	Unit
Channel to Ambient	$R_{th(ch-a)}$ [2)]	625	°C/W

[1)] Pw ≤ 10 μs, duty cycle ≤ 1%
[2)] With each pin mounted on the recommended lands

Dated: 06/01/2007

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Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
Drain Source Breakdown Voltage at I_D = 10 µA	$V_{(BR)DSS}$	30	-	-	V
Zero Gate Voltage Drain Current at V_{DS} = 30 V	I_{DSS}	-	-	1	µA
Gate Source Leakage Current at V_{GS} = ± 20 V	$\pm I_{GSS}$	-	-	1	µA
Gate Source Threshold Voltage at V_{DS} = 3 V, I_D = 100 µA	$V_{GS(th)}$	0.8	-	1.5	V
Static Drain Source On-State Resistance at V_{GS} = 4 V, I_D = 10 mA	$R_{DS(on)}$	-	-	8	Ω
Static Drain Source On-State Resistance at V_{GS} = 2.5 V, I_D = 1 mA	$R_{DS(on)}$	-	-	13	Ω
Forward Transfer Admittance at V_{DS} = 3 V, I_D = 10 mA	$\|y_{fs}\|$	20	-	-	mS
Input Capacitance at V_{DS} = 5 V, f = 1 MHz	C_{iss}	-	13	-	pF
Output Capacitance at V_{DS} = 5 V, f = 1 MHz	C_{oss}	-	9	-	pF
Reverse Transfer Capacitance at V_{DS} = 5 V, f = 1 MHz	C_{rss}	-	4	-	pF

Dated: 06/01/2007